GSM6911PJZF

60V P-Channel MOSFETs

Product Description

These P-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode.

These devices are well suited for high efficiency fast switching applications.

Features

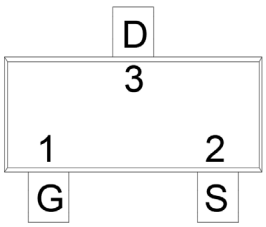
- -60V, -3.1A, $R_{DS(ON)}$=190mΩ@V_{GS}=-10V
- Improved dv/dt capability
- Fast switching
- 100% EAS Guaranteed
- Green Device Available
- SOT-23 package design
- RoHS Compliant and Halogen Free

Applications

- Motor Drive
- Power Tools
- LED Lighting

Packages & Pin Assignments

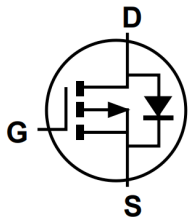
SOT-23



Top Views

Pin	Description
1	Gate
2	Source
3	Drain

Equivalent Circuit



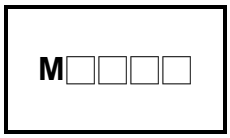
Ordering and Marking Information

Ordering Information			
Part Number	**Package**	**Part Marking**	**Quantity / Reel**
GSM6911PJZF	SOT-23	M□□□□	3,000 PCS

GSM6911P 1 2

- **Product Code:** GSM6911P
- **Package Code:** 1 is **JZ** for SOT-23
- **Green Level:** 2 is **F** for RoHS Compliant and Halogen Free

Marking Information



- **Product Code:** M
- **GS Code:** □□□□

Absolute Maximum Ratings (TA=25ºC Unless otherwise noted)

Symbol	Parameter		Value	Unit
V_{DS}	Drain-Source Voltage		-60	V
V_{GS}	Gate-Source Voltage		±20	V
I_D	Continuous Drain Current	T_A=25℃	-3.1	A
		T_A=100℃	-2	
I_{DM}	Pulsed Drain Current		-12.4	A
EAS	Single Pulse Avalanche Energy		32	mJ
IAS	Single Pulse Avalanche Current		-8	A
P_D	Power Dissipation (T_A=25℃)		1.56	W
	Power Dissipation (Derate above 25℃)		0.012	W/℃
T_J	Operating Junction Temperature Range		-50 to +150	℃
T_{STG}	Storage Temperature Range		-50 to +150	℃
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient		80	℃/W

Electrical Characteristics (T_A=25℃ Unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=-250uA	-60			V
$\triangle BV_{DSS}/\triangle T_J$	BV_{DSS} Temperature Coefficient	Reference to 25℃, I_D=-1mA		-0.05		V/℃
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=-250uA	-1.2	-1.9	-2.5	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient			5		mV/℃
I_{GSS}	Gate Leakage Current	V_{DS}=0V, V_{GS}=±20V			±100	nA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=-60V, V_{GS}=0V			-1	uA
		V_{DS}=-48V, V_{GS}=0V, T_J=125℃			-10	
I_S	Continuous Source Current	V_G=V_D=0V, Force Current			-3.1	A
I_{SM}	Pulsed Source Current				-12.4	
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS}=-10V, I_D=-3A		160	190	mΩ
		V_{GS}=-4.5V, I_D=-1.5A		200	240	
g_{FS}	Forward Transconductance	V_{DS}=-10V, I_D=-3A		3.5		S
V_{SD}	Diode Forward Voltage	V_{GS}=0V, I_S=-1A			-1	V
Dynamic characteristics						
Q_g	Total Gate Charge	V_{DS}=-30V, V_{GS}=-10V, I_D=-3A		8.2	12	nC
Q_{gs}	Gate-Source Charge			1.8	3.6	
Q_{gd}	Gate-Drain Charge			1.5	3	
C_{iss}	Input Capacitance	V_{DS}=-30V,V_{GS}=0V, f=1MHz		425	615	pF
C_{oss}	Output Capacitance			35	50	
C_{rss}	Reverse Transfer Capacitance			20	30	
$t_{d(on)}$	Turn-On Time	V_{DD}=-30V, I_D=-1A, V_{GS}=-10V, R_G=6Ω		5.2	10	ns
t_r				19	36	
$t_{d(off)}$	Turn-Off Time			35	67	
t_f				10.6	20	

Typical Performance Characteristics

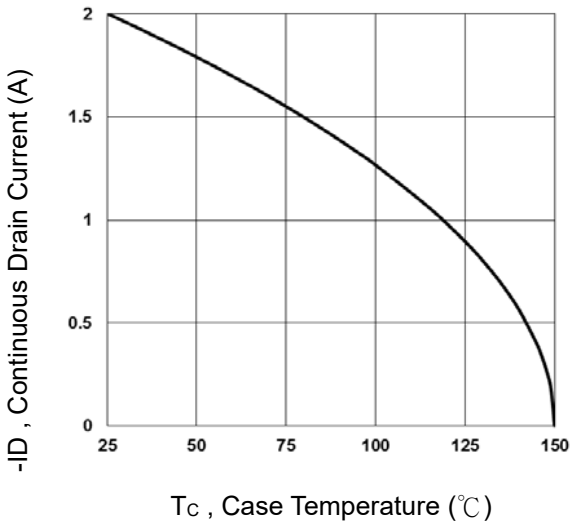


Fig.1 Continuous Drain Current vs. T_C

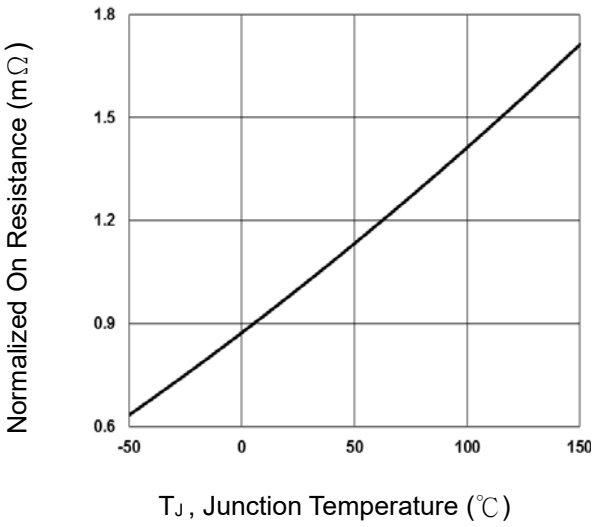


Fig.2 Normalized $RDS_{(ON)}$ vs. T_J

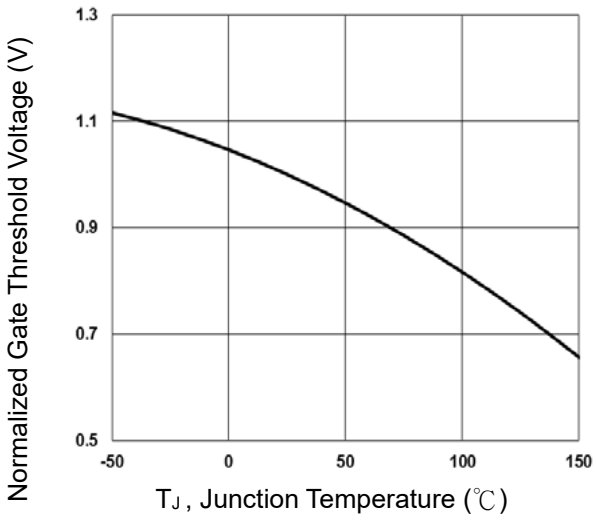


Fig.3 Normalized Vth vs. TJ

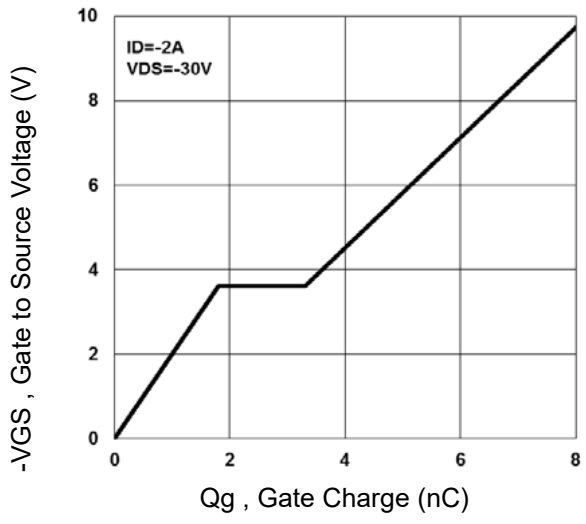


Fig.4 Gate Charge Waveform

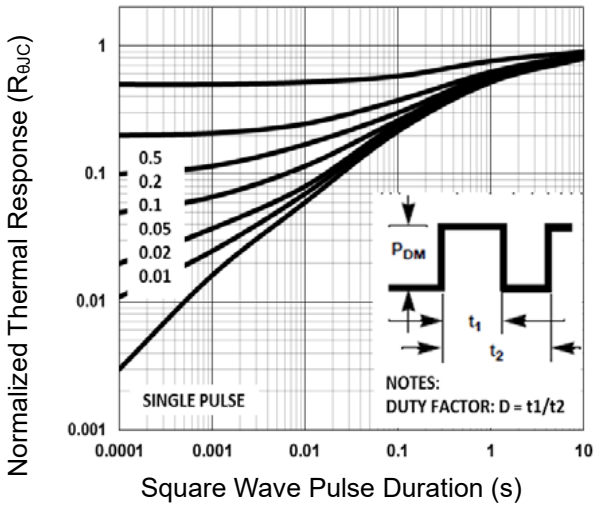


Fig.5 Normalized Transient Impedance

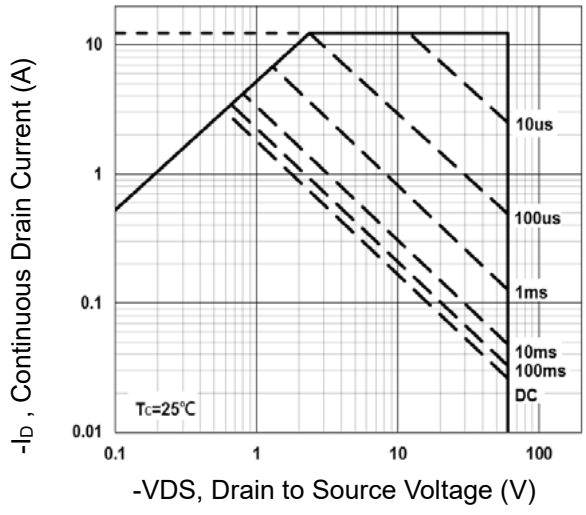
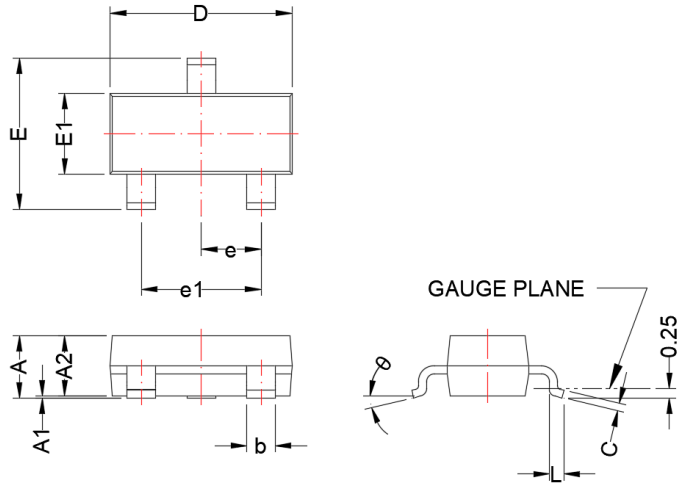


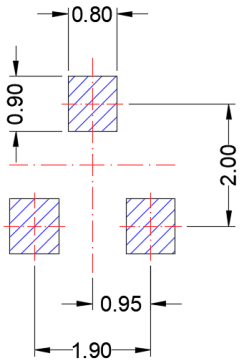
Fig.6 Maximum Safe Operation Area

SOT-23

Package Dimension



Recommended Land Pattern



Unit:mm

Dimensions				
Symbol	**Millimeters**		**Inches**	
	MIN	**MAX**	**MIN**	**MAX**
A	0.75	1.17	0.030	0.046
A1	0.01	0.15	0.000	0.006
A2	0.70	1.02	0.028	0.040
b	0.30	0.50	0.012	0.020
c	0.08	0.20	0.003	0.008
D	2.80	3.04	0.110	0.120
E	2.10	2.64	0.083	0.104
E1	1.20	1.40	0.047	0.055
e	0.95 BSC		0.037 BSC	
e1	1.90 BSC		0.075 BSC	
L	0.30	0.60	0.012	0.024
θ	0°	8°	0°	8°

NOTE:

Dimensions are exclusive of Burrs, Mold Flash & Tie Bar extrusions.

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